NSN 5961-01-319-1730

No Fiig: A110a0

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-319-1730 **Inclosure Material:** Metal and glass **Overall Length:** 1.313 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-203ab **Mounting Method:** Threaded stud **Overall Width Across Flats:** 0.678 inches Thread Size: 0.250 inches **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 45.0 repetitive peak reverse voltage and 45.0 working peak reverse voltage and 45.0 reverse voltage, instantaneous **Current Rating Per Characteristic:** 120.00 amperes forward current, average blank and 60.00 amperes forward current, average absolute and 2.00 amperes forward current, average nanoamperes and 800.00 amperes forward current, average preset **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Special Test Features:** Recovery time **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:**